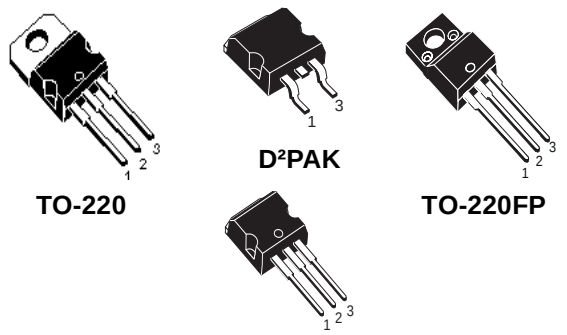
STP6NC80Z - STP6NC80ZFP
STB6NC80Z - STB6NC80Z-1

N-CHANNEL 800V - 1.5Ω - 5.4A TO-220/FP/D²PAK/I²PAK
Zener-Protected PowerMESH™III MOSFET

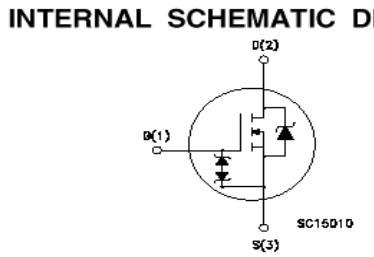
TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP6NC80Z/FP	800V	< 1.8 Ω	5.4 A
STB6NC80Z/-1	800V	< 1.8 Ω	5.4 A

- TYPICAL R_{DS}(on) = 1.5 Ω
- EXTREMELY HIGH dv/dt AND CAPABILITY GATE-TO- SOURCE ZENER DIODES
- 100% AVALANCHE TESTED
- VERY LOW GATE INPUT RESISTANCE
- GATE CHARGE MINIMIZED



DESCRIPTION

The third generation of MESH OVERLAY™ Power MOSFETs for very high voltage exhibits unsurpassed on-resistance per unit area while integrating back-to-back Zener diodes between gate and source. Such arrangement gives extra ESD capability with higher ruggedness performance as requested by a large variety of single-switch applications.



APPLICATIONS

- SINGLE-ENDED SMPS IN MONITORS, COMPUTER AND INDUSTRIAL APPLICATION
- WELDING EQUIPMENT

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP(B)6NC80Z(-1)	STP6NC80ZFP	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	800		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	800		V
V_{GS}	Gate- source Voltage	± 25		V
I_D	Drain Current (continuous) at T_C = 25°C	5.4	5.4(*)	A
I_D	Drain Current (continuous) at T_C = 100°C	3.4	3.4(*)	A
I_{DM} (1)	Drain Current (pulsed)	21	21(*)	A
P_{TOT}	Total Dissipation at T_C = 25°C	125	40	W
	Derating Factor	1	0.32	W/°C
I_{GS}	Gate-source Current (●)	±50		mA
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=15KΩ)	3		KV
dv/dt	Peak Diode Recovery voltage slope	3		V/ns
V_{ISO}	Insulation Winthstand Voltage (DC)	--	2000	V
T_{stg}	Storage Temperature	–65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤5.4A, di/dt ≤100A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ T_{JMAX}

THERMAL DATA

		TO-220 / D²PAK / I²PAK	TO-220FP	
Rthj-case	Thermal Resistance Junction-case Max	1	3.13	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	5.4	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	237	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	800			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	I_D = 1 mA, V_{GS} = 0		0.9		V/°C
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating, T_C = 125 °C			1 50	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±20V			±10	µA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 3 A		1.5	1.8	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, I_D = 3A		7		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1600 125 12		pF pF pF

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 400 V, I_D = 3 A R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		26		ns
t_r	Rise Time			10		ns
Q_g	Total Gate Charge	V_{DD} = 640V, I_D = 6A, V_{GS} = 10V		45		nC
Q_{gs}	Gate-Source Charge			12		nC
Q_{gd}	Gate-Drain Charge			18		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 640V, I_D = 6 A, R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		11		ns
t_f	Fall Time			13		ns
t_c	Cross-over Time			19		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				5.4	A
I_{SDM} (2)	Source-drain Current (pulsed)				21	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 5.4 A, V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 6 A, di/dt = 100A/µs, V_{DD} = 50V, T_j = 150°C (see test circuit, Figure 5)		850		ns
Q_{rr}	Reverse Recovery Charge			8.1		µC
I_{RRM}	Reverse Recovery Current			19		A

GATE-SOURCE ZENER DIODE

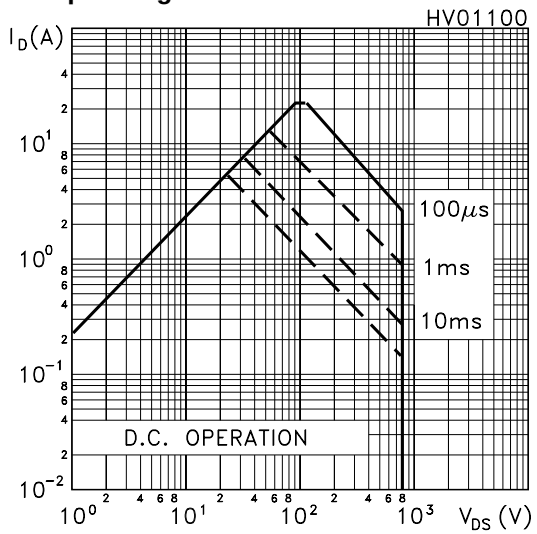
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	Igs=± 1mA (Open Drain)	25			V
αT	Voltage Thermal Coefficient	T=25°C Note(3)		1.3		10^{-4}/°C
Rz	Dynamic Resistance	I_D = 50 mA, V_{GS} = 0		90		Ω

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $\Delta V_{BV} = \alpha T\ (25°\text{-}T)\ BV_{GSO}(25°)$

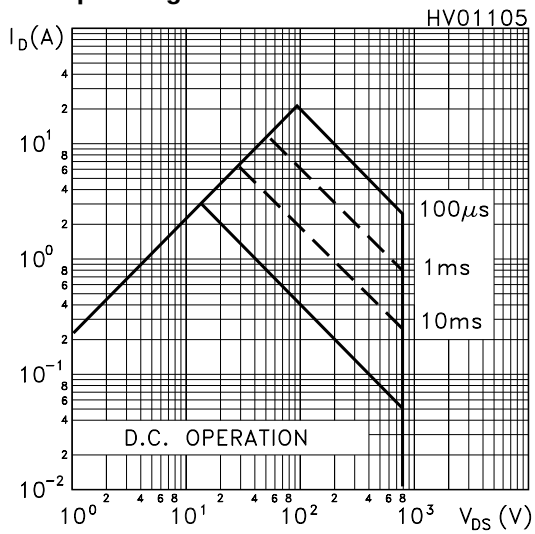
PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

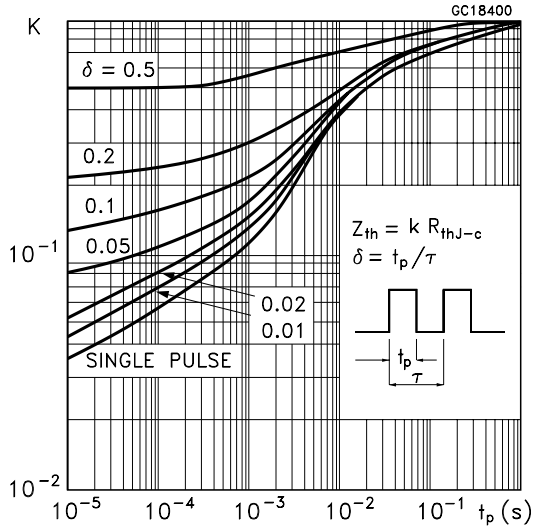
Safe Operating Area For TO-220 /D²PAK/I²PAK



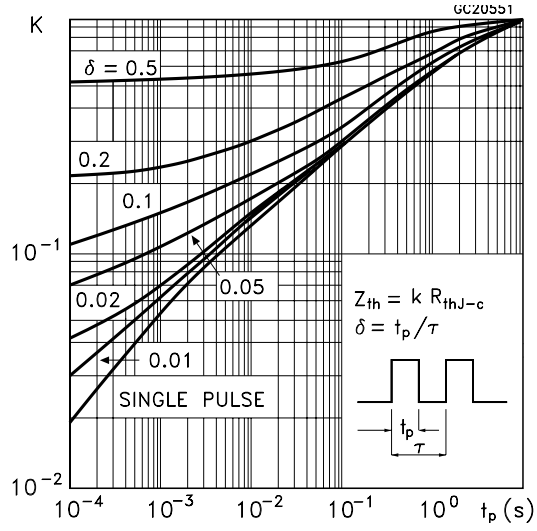
Safe Operating Area For TO-220FP



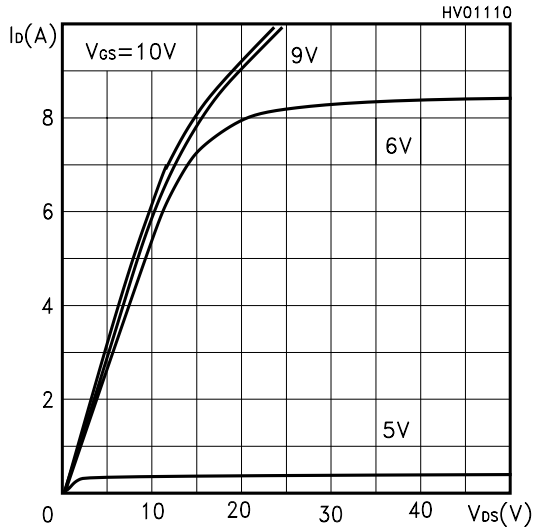
Thermal Impedance For TO-220 /D²PAK/I²PAK



Thermal Impedance For TO-220FP



Output Characteristics



Transfer Characteristics